

RF CONDITIONING AND TESTS ON TTF-III POWER COUPLEURS AT LAL (Interlock thresholds)

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LAL, February 16th 2007

RF conditioning procedure principle



DESY conditioning procedure parameters :

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	1 st threshold	2 x 10 ⁻⁷ mbar	\implies $P_{i+1} = P_i - \Delta P$
Vacuum	2 nd threshold	4 x 10 ⁻⁷ mbar	\implies P _{1,4} = P ₁ - 4x Δ P
	Vacuum interlock limit	1 x 10 ⁻⁶ mbar)
e- current	Current interlock limit	5 mA	Stop power
Light	PM interlock limit	1 Lux	
Temperature	I. R. detector limit	85 °C	immediately
Arcs	If any		
Repetition rate	2 Hz		
Control loop	30 s		

Coupler RF conditioning

Large spread of conditioning time \approx 50 h to \approx 200 h

The first conditioning step is the most time consuming



In-situ baking effect



In average in-situ baked conditioning time \approx 40% of the non in-situ baked one for the TTF-III couplers

We have to verify that this huge difference is not due to some dissimilarities between pairs of couplers



Verification :

Exp1:

$$T_{CondBaked} / T_{CondN.Baked} = 25$$

Exp2:
 $T_{CondBaked} / T_{CondN.Baked} = 52$

Spectra comparison

Mass spectrum : before conditioning (baked & unbaked couplers)

Despite the long conditioning time in the non in-situ baked case, we can't reach vacuum levels as good as in the in-situ baked one.



Mass spectrum: after conditioning (baked & unbaked couplers)



Optimisation of the vacuum thresholds (1)



During conditioning, there were periods in which the conditioning progress were slowed down by continuous vacuum level fluctuations in the absence of significant e- current signals (5h to rise power from 80 kW to 117 kW in this example).

Low electron bombardment action on surfaces during this periods.

Possible solution: Using **6 10**-7 **mbar** as a first threshold may avoid this conditioning stage

Calculation on the performances of the pumping system has been worked out in order to chose new vacuum thresholds

Optimisation of the vacuum thresholds (2)

The new chosen values:

First threshold :	6 10 ⁻⁷ mbar
Second threshold:	10 ⁻⁶ mbar
Vacuum interlock limits:	5 10 ⁻⁶ mbar



The duration of these steps depends only on the time required by the monitoring program to increase the RF power 7

Optimisation of procedure speed (1)

The power control loop duration is 30 s

Criteria :

"The pumping system should have enough time to pump a pressure rise near to the vacuum interlock limit (5x10⁻⁶ mbar) down to less than the first threshold value (6x10⁻⁷ mbar) during only one delay time of the loop, if the event causing this vacuum burst vanishes."



Optimisation of procedure speed (2)

To have a security margin we decide to take three times this value as a new loop time delay: **15 s (3 x 5 s)**



Conditioning time decrease

Less e- current magnitude reduction before reaching high power levels in the first conditioning step (20 µs)

Increase the pulse rate



Increase of the pulse rate



4 Hz pulse rate => no more ecurrent interlocks at 550 kW

Conditioning time is also \approx 20 h



Last conditioning time performances



Antenna DC biased TTF-III coupler

DC bias:

V = +4.5 kV

DC Bias was applied to already conditioned couplers

٩W





Future

TTF-III coupler



Pick-up & PM diagnostics will be omitted



- Pick-up E- current acquisition:
- ➢Polarization: 30 V
- ➢Interlock threshold: 5 mA
- >Information about the event location:
 - ✓ Near warm window
 - ✓Near the worm side of the cold window
 - ✓Near the cold side of the cold window

- Inner conductor E- current acquisition:
- ➢Polarization: ?
- >Interlock threshold: ?
- >Information about the event location:

No information about the e- event location

First tests for e- current measurements with the inner conductor

DESY Tests:

Large dependence of the e- current characteristics (value, shape, and sign) to the polarization value



Bias 0V (20mA, 4ms per div.)

LAL tests: (bias = 30 V)

≻Huge current on the inner conductor with large dynamic range during conditioning (up to ~A at the start of conditioning to ~mA at the end)

➢No conclusion about a new secure e- currents thresholds relative to the inner conductor acquisition, but there is correlation between vacuum and the measured current rise.



Bias 100V (50mA, 4ms per div.)



Bias 120V (50mA, 4ms per div.)



20 µs pulse; max current 2.4 A

1300 μs pulse; current ~ few mAs

More experiments are needed to establish new e- current thresholds

Conclusion

□New conditioning time performances : ~20 h

□4.5 kV DC bias of the inner conductor seems to be efficient to stop e- activity on TTF-III coupler

□More tests are needed to find the best way to use the coupler inner conductor for e- current measurements

Example of e- pick-ups signals (Polarisation = 30 V)



Storage effect on conditioned couplers



 Δ T: [Duration of the second conditioning (after storage)] – [Time of the processing program]

Experiment N°	In-situ baking before the 1 st conditioning	Storage duration	ΔΤ
1	yes	Few hours	0
2	no	1.5 month	58 h
3	yes	2 months	3 h

The current storage procedure seems to preserve the conditioning memory if couplers were in-situ baked before their conditioning 18

2 MW power test on TTF-III coupler (TW)



Conditioned TTF-III couplers (Pmax = 1 MW) don't need extra conditioning to reach 2 MW at 20 µs.



20 µs